

VHF POWER MOSFET

N-Channel Enhancement Mode

DESCRIPTION:

The **VFT30-28** is a gold metallized N-Channel enhancement mode MOSFET, intended for use in 28VDC large signal applications up to 400MHz.

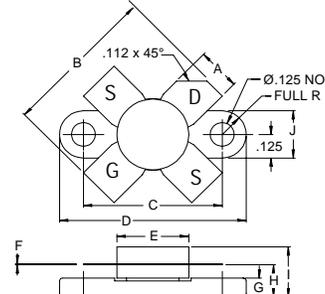
FEATURES:

- $P_G = 14$ dB Typ. at 30 W /175MHz
- **10:1 Load VSWR** Capability
- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|---------------|---------------------------------|
| I_D | 5.0 A |
| $V_{(BR)DSS}$ | 65 V |
| V_{DGR} | 65 V |
| V_{GS} | ± 40 V |
| P_{DISS} | 100 W @ $T_C = 25^\circ C$ |
| T_J | $-65^\circ C$ to $+200^\circ C$ |
| T_{STG} | $-65^\circ C$ to $+150^\circ C$ |
| θ_{JC} | 1.75 $^\circ C/W$ |

PACKAGE STYLE .380 4L FLG



| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|-----|------------------------|------------------------|
| A | .220 / 5.59 | .230 / 5.84 |
| B | .785 / 19.94 | |
| C | .720 / 18.29 | .730 / 18.54 |
| D | .970 / 24.64 | .980 / 24.89 |
| E | | .385 / 9.78 |
| F | .004 / 0.10 | .006 / 0.15 |
| G | .085 / 2.16 | .105 / 2.67 |
| H | .160 / 4.06 | .180 / 4.57 |
| I | | .280 / 7.11 |
| J | .240 / 6.10 | .255 / 6.48 |

ORDER CODE: ASI10703

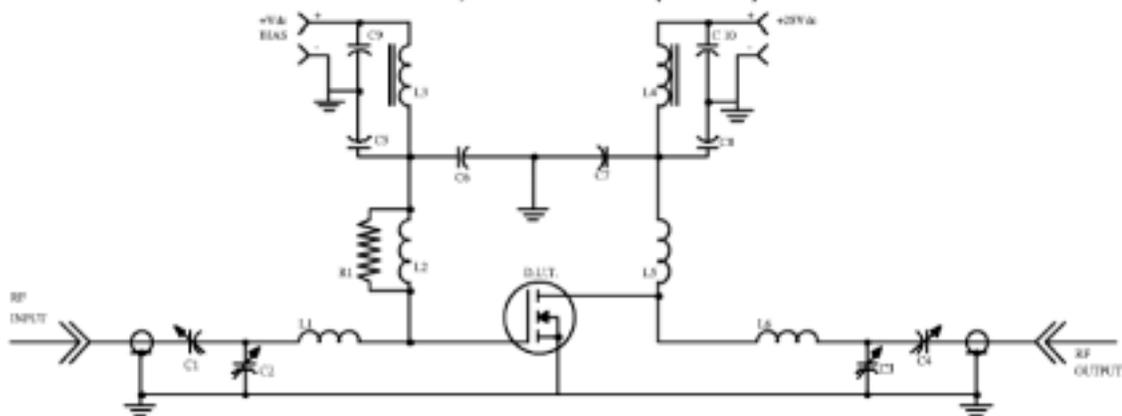
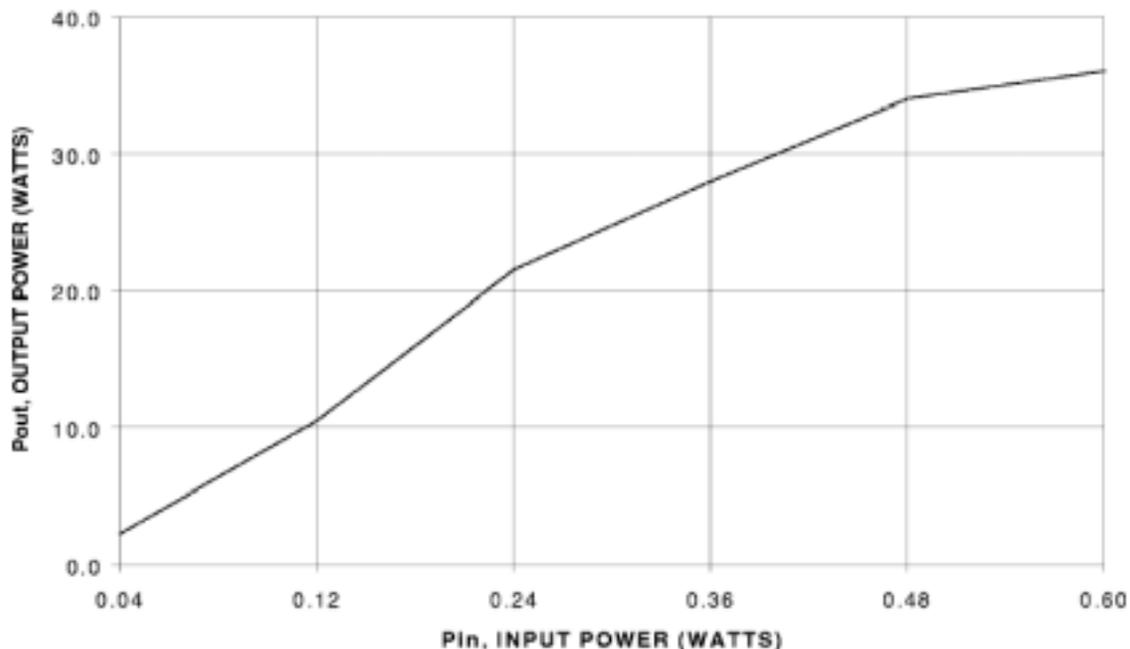
CHARACTERISTICS $T_C = 25^\circ C$

| SYMBOL | TEST CONDITIONS | | | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|---------------|-----------------|------------------|---------------|---------|---------|---------|---------|
| $V_{(BR)DSS}$ | $V_{GS} = 0$ V | $I_{DS} = 10$ mA | | 60 | --- | --- | V |
| I_{DSS} | $V_{DS} = 28$ V | $V_{GS} = 0$ V | | --- | --- | 4.0 | mA |
| I_{GSS} | $V_{DS} = 0$ V | $V_{GS} = 20$ V | | --- | --- | 1.0 | μA |
| V_{GS} | $V_{DS} = 10$ V | $I_D = 25$ mA | | 1.0 | --- | 6.0 | V |
| G_{FS} | $V_{DS} = 10$ V | $I_D = 500$ mA | | 0.5 | --- | --- | mho |
| C_{iss} | $V_{DS} = 28$ V | $V_{GS} = 0$ V | $f = 1.0$ MHz | | 46 | | pF |
| C_{oss} | | | | | 33 | | |
| C_{rss} | | | | | 6.0 | | |

CHARACTERISTICS $T_C = 25^\circ\text{C}$

| SYMBOL | TEST CONDITIONS | | | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|----------|-------------------------|-------------------------|-------------------------|---------|---------|---------|-----------|
| P_G | $V_{DD} = 28\text{ V}$ | $I_{DQ} = 25\text{ mA}$ | $P_{OUT} = 30\text{ W}$ | 13 | 14 | | dB |
| η_D | $P_{IN} = 1.5\text{ W}$ | | $f = 175\text{ MHz}$ | 50 | 60 | | % |

Power Out vs Power In



- | | | | |
|----|--|-----|--|
| R1 | 55 Ohm, 1/2 Watt | C8 | 100pF, Chip Capacitor |
| C1 | ARC0, 4423 16pF - 30pF Variable Capacitor | C9 | 10uF, 63V Electrolytic Capacitor |
| C2 | ARC0, 4463 20pF - 100pF Variable Capacitor | C10 | 10uF, 63V Electrolytic Capacitor |
| C3 | ARC0, 4463 10pF - 80pF Variable Capacitor | L1 | 820 AWG, 2 Turns, 0.25" ID, 19uH |
| C4 | ARC0, 4423 16pF - 30pF Variable Capacitor | L2 | 820 AWG, 6 Turns, 0.25" ID, On R1, 206uH |
| C5 | 100pF, Chip Capacitor | L3 | Fair-Rite P/N 2943666661 |
| C6 | UNELCO, 100pF Chip Capacitor | L4 | Fair-Rite P/N 2943666661 |
| C7 | UNELCO, 100pF Chip Capacitor | L5 | 820 AWG, 6 Turns, 0.25" ID, 206uH |
| | | L6 | 820 AWG, 2 Turns, 0.25" ID, 19uH |